

YJ Planar Schottky Barrier Diode Die Specification

100V 5A, 68mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB068S100SS-280A

Main Products Characterstics

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 5\text{ A}$

$\leq 2\%$

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Note: 1 * : Also can offer device with 8 mils thickness
- 2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

does not guarantee device performance after 330 days of storage (x-one)

BDC 49.16 70.8 530.5 70488 rework BT F3 6.72 Tf1 0 0 1 87.02493.3